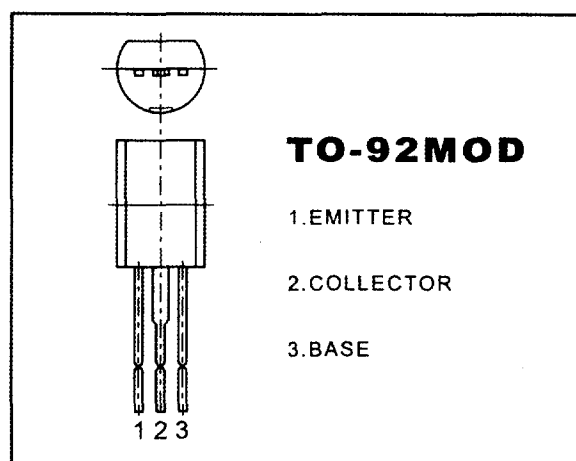


TO-92MOD Plastic-Encapsulate Transistors

2SC2060 TRANSISTOR(NPN)



FEATURES

Power dissipation

P_{CM} : 0.75W ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : 1 A

Collector-base voltage

$V_{(BR)CBO}$: 40 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

ELECTRICAL CHARACTERISTICS

($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 100 \mu A, I_E = 0$	40		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 1 mA, I_B = 0$	32		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 100 \mu A, I_C = 0$	5		V
Collector cut-off current	I_{CBO}	$V_{CB} = 40 V, I_E = 0$		0.5	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 4 V, I_C = 0$		0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = 3 V, I_C = 100 mA$	80	400	
Collector-emitter saturation voltage	V_{CEsat}	$I_C = 500 mA, I_B = 50 mA$		0.4	V